

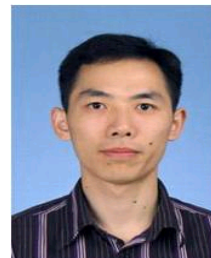


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现在位置: [首页](#) > [人才队伍](#) > [副研究员](#)

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简历:

彭铭曾, 男, 硕士生导师。毕业于中国科学院物理研究所, 2008年获得理学博士学位, 主要从事GaN基材料的MOCVD生长和物性研究及其在发光二极管、紫外探测器和高频功率器件方面的应用。毕业后在中国科学院微电子研究所开展GaN基微波功率材料、器件关键工艺和单片集成技术方面的研究工作。2012年9月至今为中国科学院北京纳米能源与系统研究所副研究员。目前在国内外发表有关GaN基宽禁带半导体材料和器件方面研究论文30余篇, 已申请发明专利8项, 授权2项, 参加国际会议2次。

研究方向:

专家类别:

副研究员

职务:

社会任职:

承担科研项目情况:

获奖及荣誉:

1) 2008年中科院物理所三好学生

代表论著:

- 1) M.Z. Peng, Y.K. Zheng, Q. Ge, K. Wei, X.Y. Liu, Effect of pinch-off current leakage characteristics on microwave power performances of Al_xGa_{1-x}N/GaN HEMTs, Solid State Electronics, 80, 1~4 (2013).
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- 3) M.Z. Peng, Y. K. Zheng, X. J. Chen, X. Y. Liu. GaN-based HEMT devices for power switching applications. 2012 International Workshop on Microwave and Millimeter Wave Circuits and System Technology (2012).
- 4) M.Z. Peng, Y. K. Zheng, W. Ke, X. J. Chen, X. Y. Liu. High-performance single-chip Ga_N HEMT power amplifiers for X-band applications. 2011 World Congress of Engineering and Technology (2011).
- 5) M.Z. Peng, Y. K. Zheng, W. Ke, X. J. Chen, X. Y. Liu. X-band AlGa_N/Ga_N HEMTs with high microwave power performance. Sci China Phys Mech Astron. 54, 442~445 (2011).
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- 8) M.Z. Peng, L.W. Guo, J. Zhang, et al. Reducing dislocations of Al-rich AlGa_N by combining AlN buffer and AlN/Al_{0.8}Ga_{0.2}N superlattices. JOURNAL OF CRYSTAL GROWTH. 310 (6), 1088~1092 (2008).

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11) M.Z. Peng, J. Zhang, X.L. Zhu, et al. Electrical and optical properties of n-type Al_xGa_{1-x}N. LASER & INFRARED. 36, 1057 (2006).